



#### **60V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223**

#### **Features**

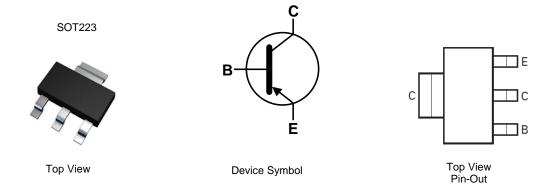
- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -5.5A High Continuous Collector Current
- I<sub>CM</sub> = -15A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -70mV @ -1A</li>
- R<sub>SAT</sub> = 39mΩ for a Low Equivalent On-Resistance
- hFE Specified Up to -10A for a High Gain Hold Up
- Complementary NPN Type: ZX5T851G
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
   Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)

#### **Applications**

- DC-DC Converters
- MOSFET & IGBT Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control



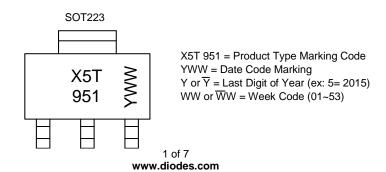
#### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T951GTA	X5T951	7	12	1,000
ZX5T951GTC	X5T951	13	12	4,000

Notes

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

#### **Marking Information**



ZX5T951G Datasheet Number: DS33424 Rev. 4 - 2



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-100	V
Collector-Emitter Voltage	$V_{CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-5.5	Α
Peak Pulse Current	I <sub>CM</sub>	-15	A

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	0	3.0 24	W	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	mW /°C	
Thermal Decistores, Junction to Ambient	(Note 5)	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance Junction to Lead (Note 7)		$R_{ heta JL}$	10.48		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

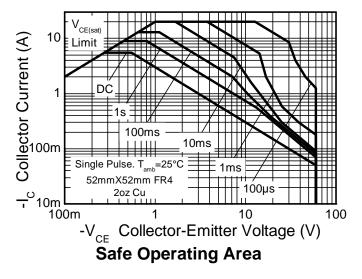
- 5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note (5), except the device is surface mounted on 25mm x 25mm with 1oz copper.

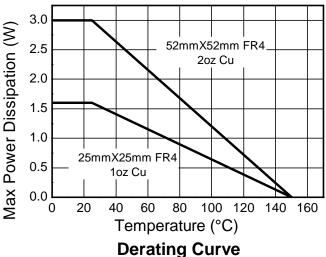
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).

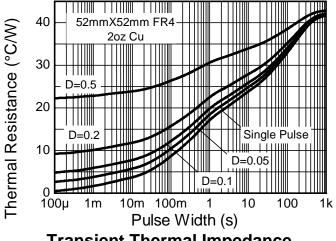
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

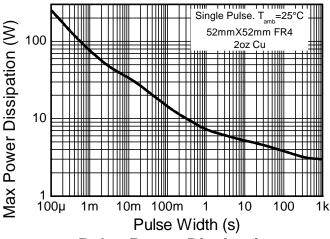


## **Thermal Characteristics and Derating Information**









**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



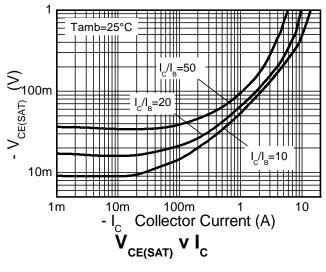
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

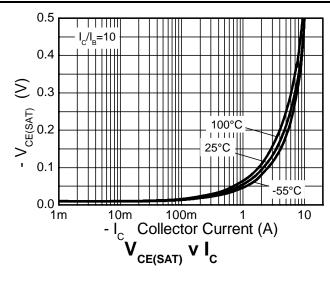
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-100	-120	-	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-100	-120	-	V	$I_C = -1\mu A$ , RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-60	-80	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.1	-	V	I <sub>E</sub> = -100μA
Collector-Base Cutoff Current	I <sub>CBO</sub>	-	<1 -	-20 -0.5	nΑ μΑ	V <sub>CB</sub> = -80V V <sub>CB</sub> = -80V, T <sub>A</sub> = +100°C
Collector-Emitter Cutoff Current	I <sub>CER</sub> R ≤ 1kΩ	-	<1 -	-20 -0.5	nΑ μΑ	V <sub>CB</sub> = -80V V <sub>CB</sub> = -80V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	-	<1	-10	nA	$V_{EB} = -6V$
		100	250	-		$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
Static Forward Current Transfer Datic (Note 0)	h <sub>FE</sub>	100	200	300		$I_C = -2A$ , $V_{CE} = -1V$
Static Forward Current Transfer Ratio (Note 9)		45	90	-	-	$I_{C} = -5A$ , $V_{CE} = -1V$
		10	25	-		$I_C = -10A$ , $V_{CE} = -1V$
	V <sub>CE(sat)</sub>	-	-15	-25	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector Emitter Seturation Voltage (Note 0)		-	-55	-70		$I_C = -1A$ , $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 9)		-	-90	-120		$I_C = -2A$ , $I_B = -200mA$
		-	-195	-250		$I_C = -5A$ , $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	-1,030	-1,150	mV	$I_C = -5A$ , $I_B = -500$ mV
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	-920	-1,020	mV	$I_{C} = -5A$ , $V_{CE} = -1V$
Output Capacitance (Note 9)	$C_obo$	-	48	-	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	-	120	-	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -100mA f = 50MHz
Switching Time	t <sub>on</sub>	-	39	-	ns	$V_{CC} = -10V, I_{C} = -1A$
Switching Time	t <sub>off</sub>	-	370	-	115	$I_{B1} = -I_{B2} = -100 \text{mA}$

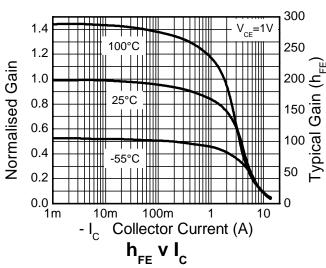
Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.

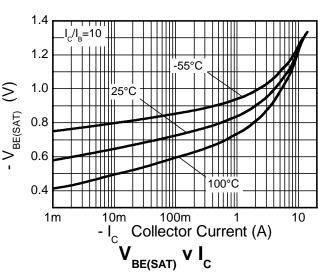


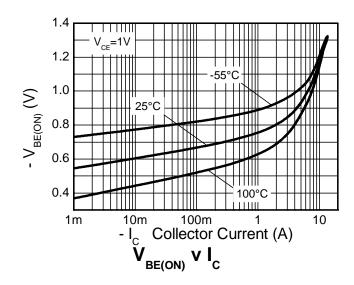
### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)







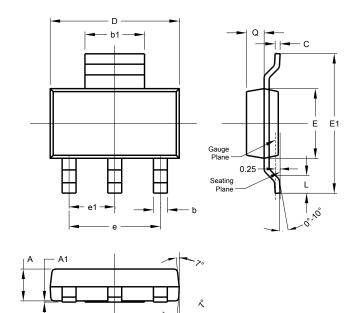






### **Package Outline Dimensions**

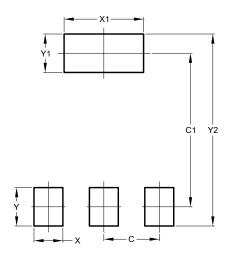
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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